

Test Beam Measurements with 3D Silicon Strip Detectors (Fabricated by FBK-IRST and CNM-IMB)

Michael Köhler¹, Richard Bates², Gian-Franco Dalla Betta³, Maurizio Boscardin⁴,
Simon Eckert¹, Celeste Fleta⁵, Jaakko Härkönen⁶, Sarah Houston², Karl Jakobs¹,
Susanne Kühn¹, Manuel Lozano⁵, Panja-Riina Luukka⁶, Teppo Mäenpää⁶, Henri
Moilanen⁶, Gregor Pahn¹, Chris Parkes², Giulio Pellegrini⁵, Ulrich Parzefall¹,
Sabina Ronchin⁴, Andrea Zoboli³, Nicola Zorzi⁴

¹University of Freiburg

²University of Glasgow

³INFN and University of Trento

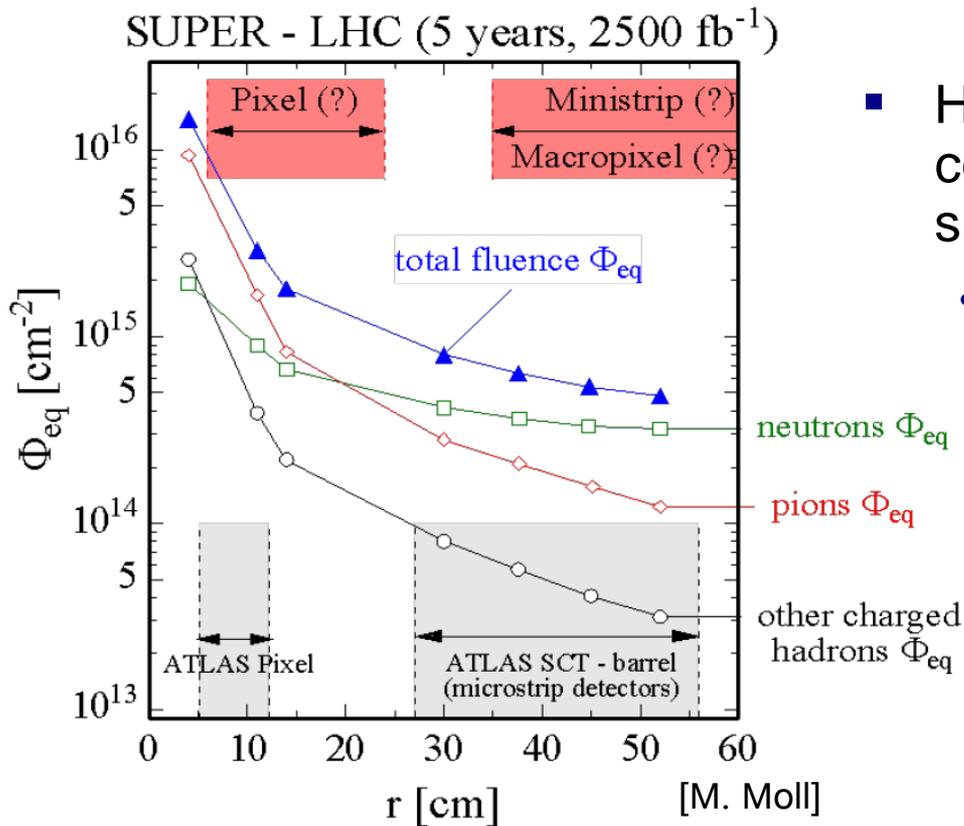
⁴FBK-IRST, Trento

⁵CNM-IMB, Barcelona

⁶Helsinki Institute of Physics

SLHC: More Radiation Hardness Needed

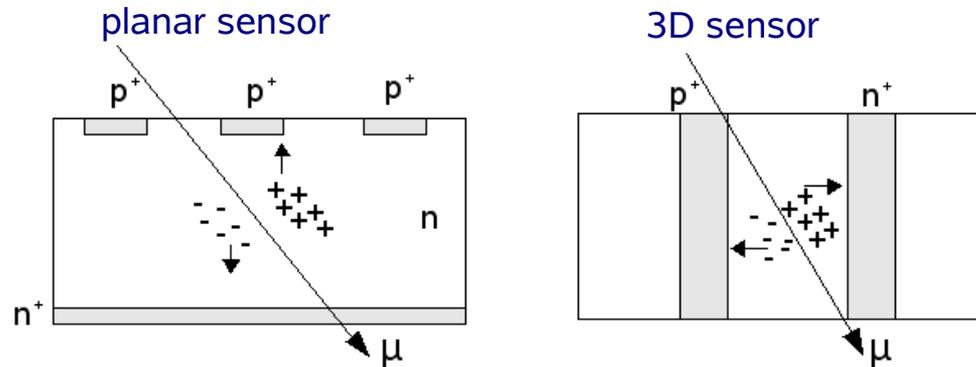
- ~ 2019: luminosity upgrade of the LHC (super LHC)
 → **Peak luminosity increased tenfold**: $L=10^{35} \text{ cm}^{-2} \text{ s}^{-1}$



- High radiation level causes considerable **radiation damage** in silicon tracking detectors
 - New technologies needed** for the tracking detectors, especially for the inner layers!

3D Detectors

- Decoupling of thickness and distance for charge collection: **columnar electrodes** are etched into the sensor and doped
 - **Lower depletion voltage, lower trapping**



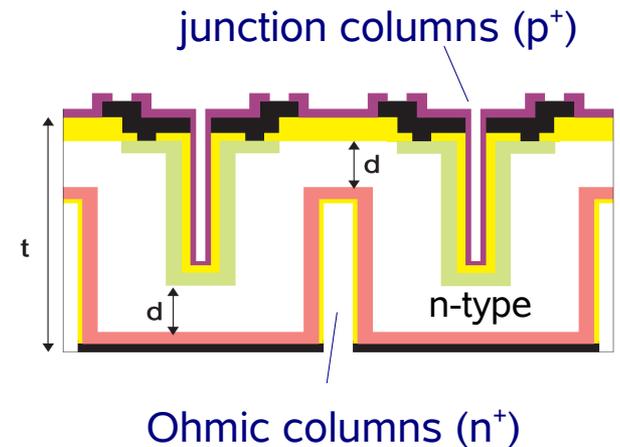
- Fabrication of 3D detectors challenging – modified designs under investigation

3D-DDTC

- FBK-IRST (Trento) and CNM (Barcelona): **3D-DDTC** (double-sided, double type column)

- Columns etched into the wafer from both sides, but **not fully penetrating**

- Process much simpler than full 3D detectors: less production steps, no support wafer required



- General designs of both manufacturers similar, but:

FBK:

- Columns unfilled
- Ohmic columns connected by uniform n^+ -doping layer and metallisation
- AC and DC coupled readout pads

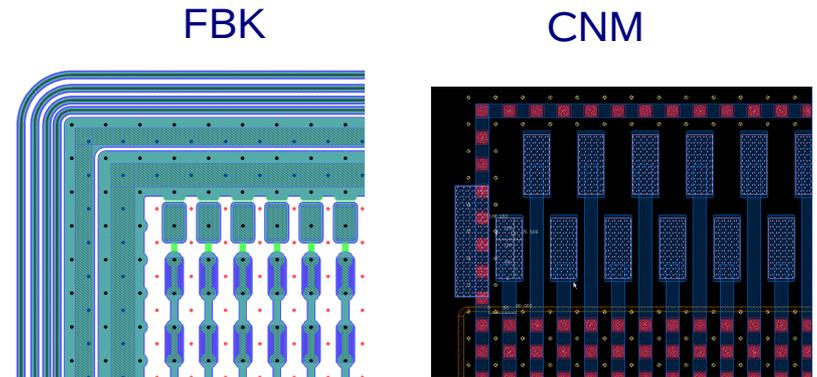
CNM:

- Columns partially filled with Poly-Silicon
- Ohmic columns connected by Poly-Silicon and metallisation
- DC coupled readout pads

Devices Under Test

- Two devices under test (produced by **FBK and CNM**)
 - Of both manufacturers: **first 3D-DDTC batches** ever produced
 - Perfect performance not expected!
- Columns on “front” side (p^+ -doped) are joined to strips
- Detector properties:**

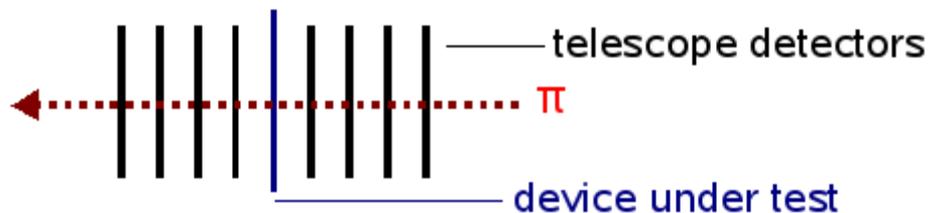
Property	FBK	CNM
Substrate Thickness	300 μm	285 μm
Substrate type	n-type (FZ)	n-type (FZ)
Strip pitch, column spacing in strips	100 μm	80 μm
Depth of junction columns (front side)	190 μm	250 μm
Depth of Ohmic columns (back side)	160 μm	250 μm
Strip Length	8.1 mm	4 mm
Number of Strip	81	50



- Although 3D detectors are currently **mainly a candidate for the sLHC pixel layers**, it is still worth studying 3D detectors with strip design – the readout is much simpler

Test Beam July 2008

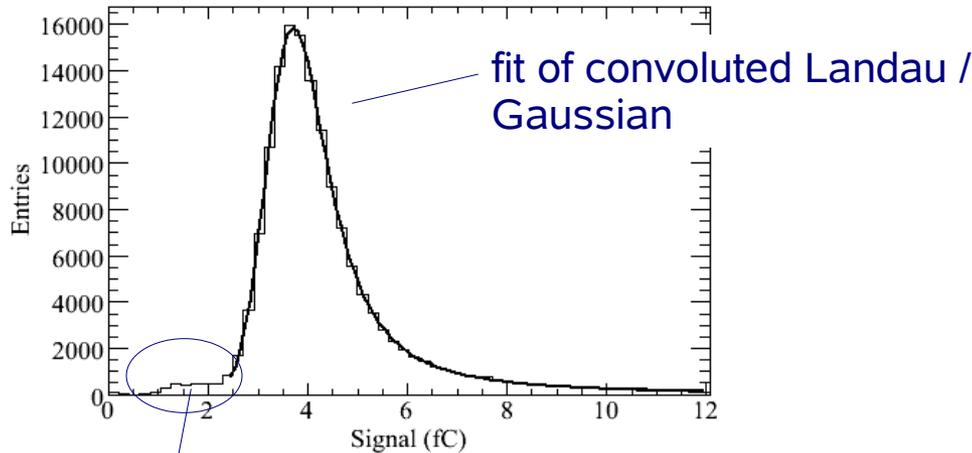
- CERN SPS, H2 beamline, 225 GeV/c pions
- Test beam in the framework of **RD50 and CMS**, organised by the University of Helsinki
- **Silicon Beam Telescope (SiBT)**, resolution $\approx 4 \mu\text{m}$
- Sensor positioned perpendicular to the beam
- Readout with **CMS hardware**
- Front-end chip: **APV25** (50 ns shaping time)



Signal Spectrum at 40 V Bias (FBK)

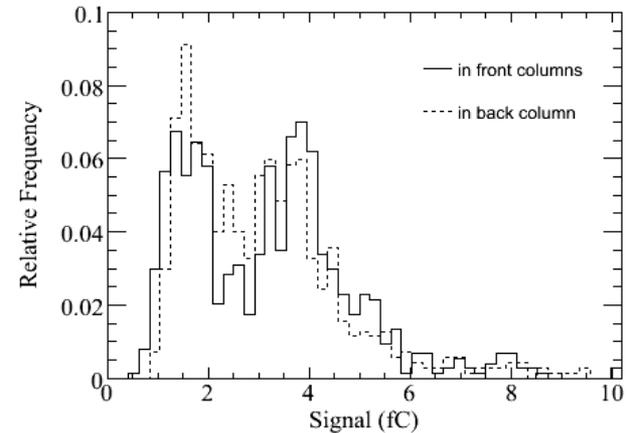
- Sum of **signal of the two strips closest to the track** point of impact

all tracks:

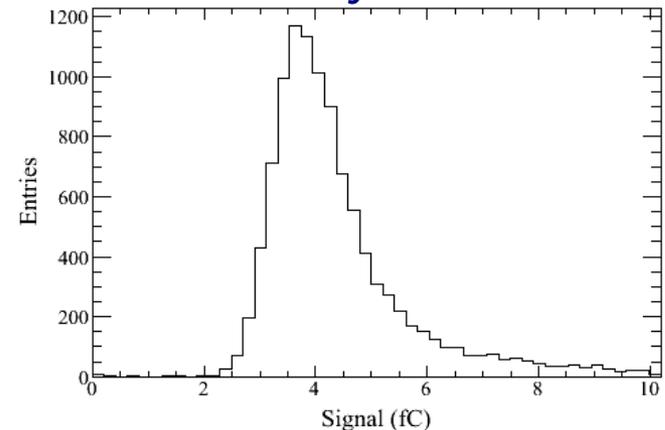


contribution from particles going through the columns

tracks in front and back columns:



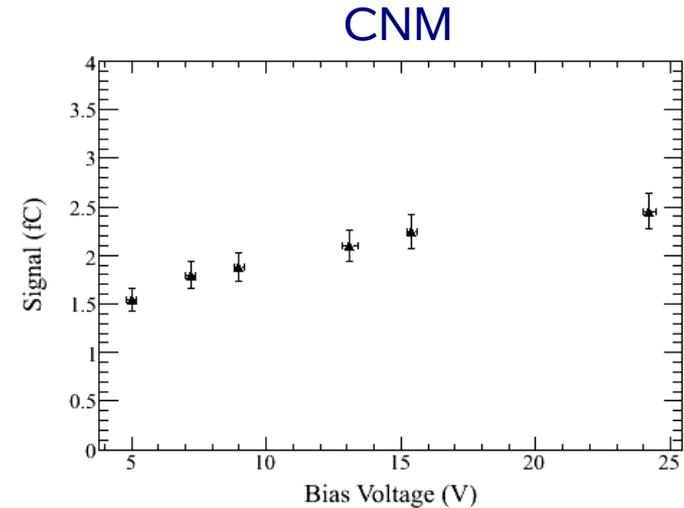
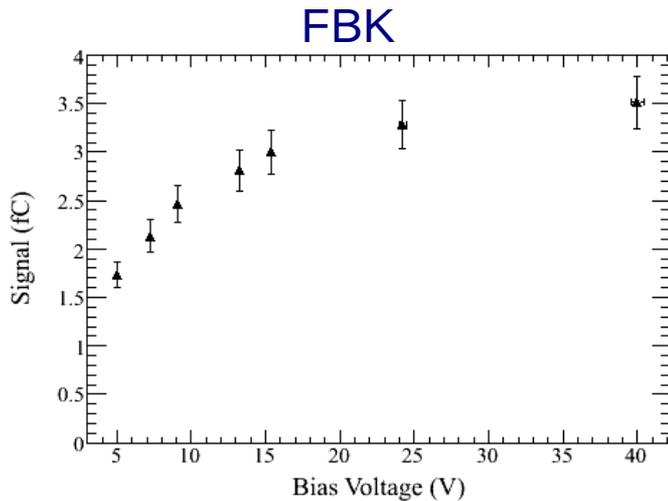
tracks far away from columns:



- Tracks crossing the hollow columns:
charge deposition only in silicon below the columns

Signal Versus Bias

- Landau MPV vs bias voltage (clusters of both strips closest to track)



- FBK detector:**

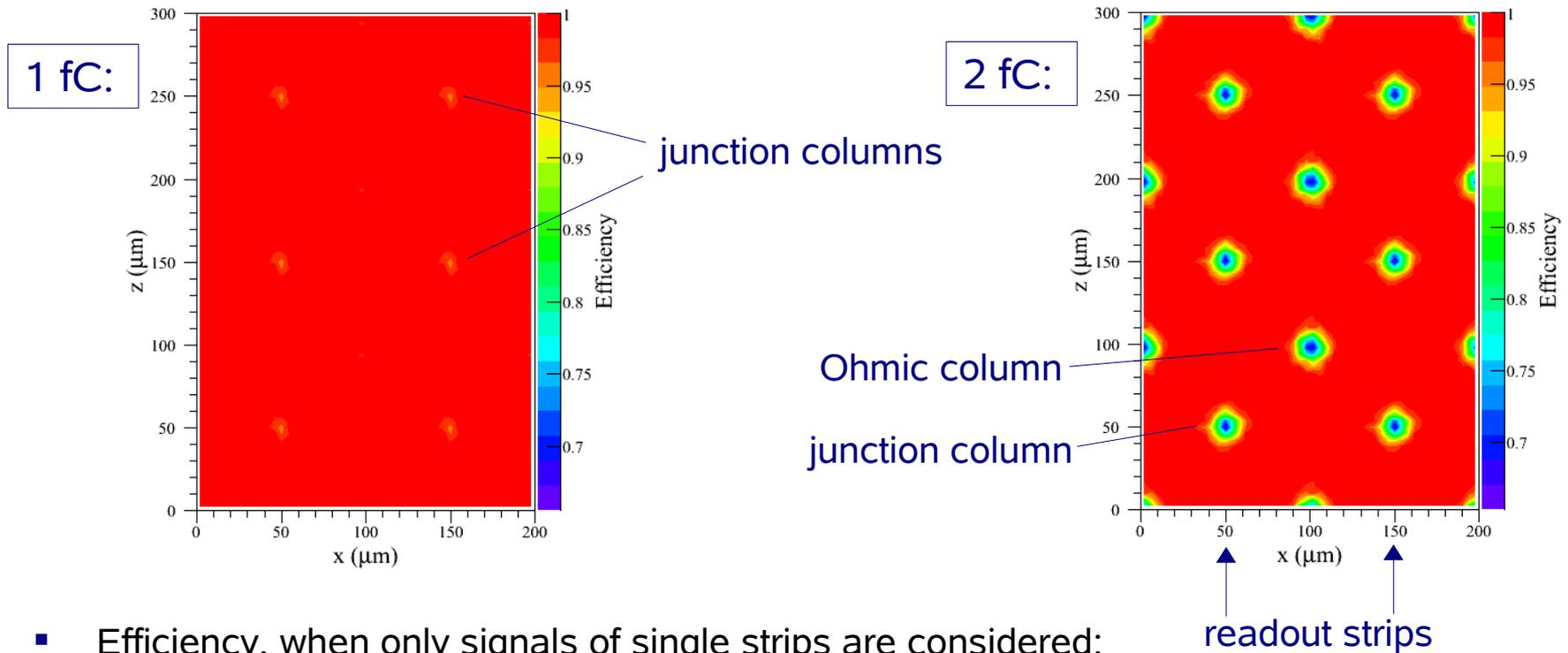
- Max. signal at 40 V: (3.5 ± 0.3) fC, (22 ± 2) ke⁻, S/N ~31
- Expected for 300 μ m silicon: 3.7 fC, 23 ke⁻
- Measured signal in agreement with expected signal

- CNM detector:**

- Max. signal at 24 V: (2.5 ± 0.2) fC, (15.6 ± 1.2) ke⁻, S/N ~30
- Expected for 285 μ m silicon: 3.5 fC, 22 ke⁻
- Max. signal ~30% lower than expected (detectors are from very first batch!)

2D Efficiency (FBK)

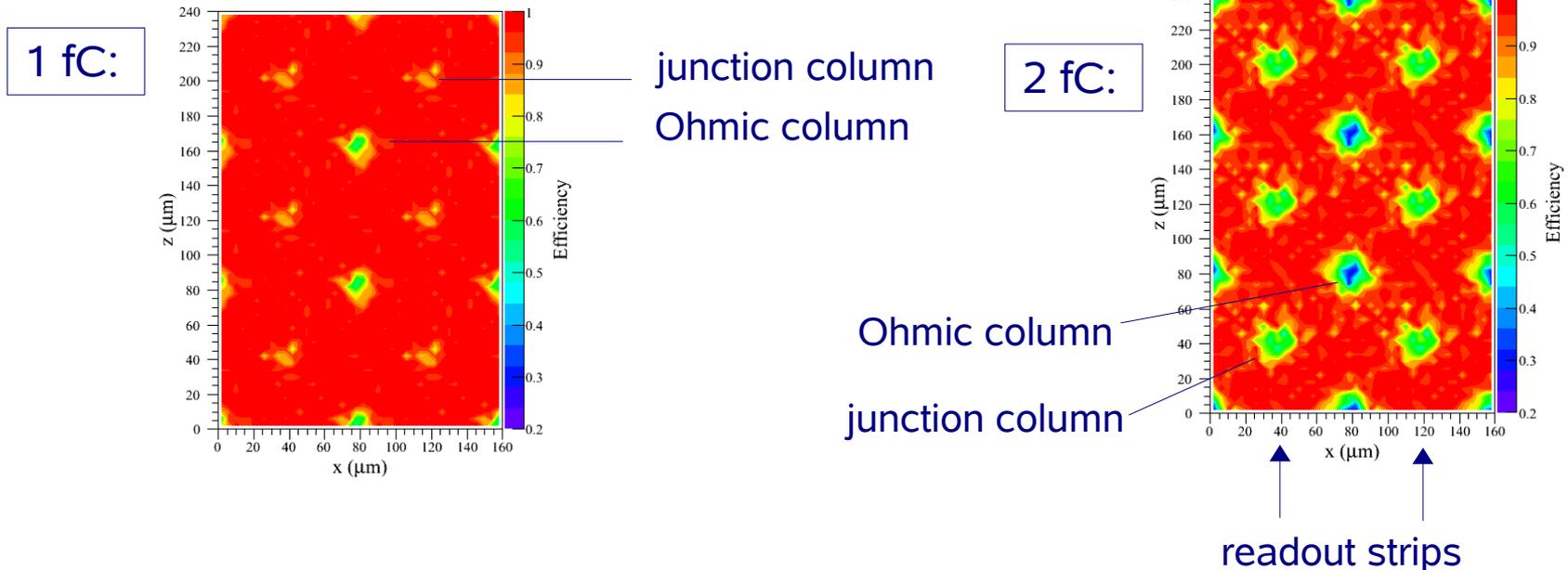
- Data superimposed onto unit cell – unit cell plotted six times side by side
- **Bias: 40V, signals of two strips** adjacent to the track position summed up
 - At 1 fC threshold: Eff. = $(99.80 \pm 0.01)\%$
 - At 2 fC threshold: Eff. = $(98.53 \pm 0.03)\%$ - column structure clearly visible



- Efficiency, when only signals of single strips are considered:
 - at 1 fC: $(99.46 \pm 0.02)\%$, at 2 fC: $(97.29 \pm 0.04)\%$

2D Efficiency (CNM)

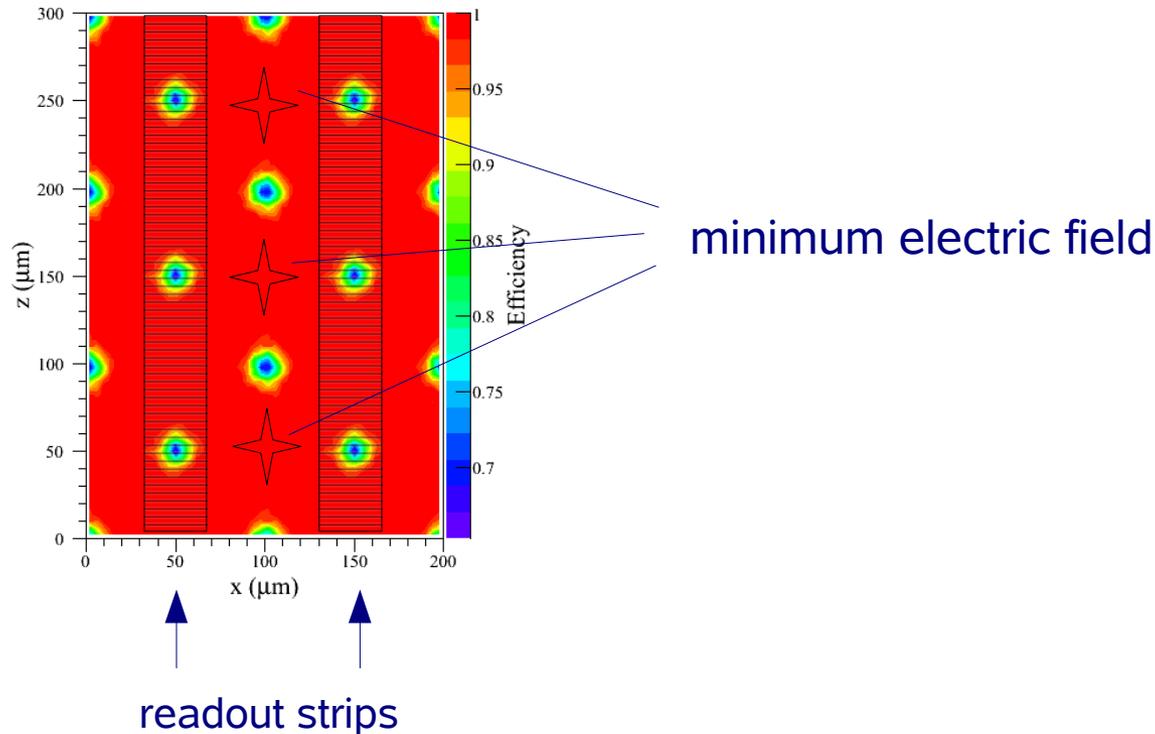
- More fluctuations than in plots for FBK sensor due to **lower statistics**
- Bias: 24V, signals of two strips** adjacent to the track position summed up
 - At 1 fC threshold: Eff. = $(97.9 \pm 0.2)\%$ - column structure visible
 - At 2 fC threshold: Eff. = $(92.1 \pm 0.3)\%$



- Efficiency, when only signals of single strips are considered:
 - at 1 fC: $(97.5 \pm 0.2)\%$, at 2 fC: $(90.4 \pm 0.3)\%$

Low Field Region

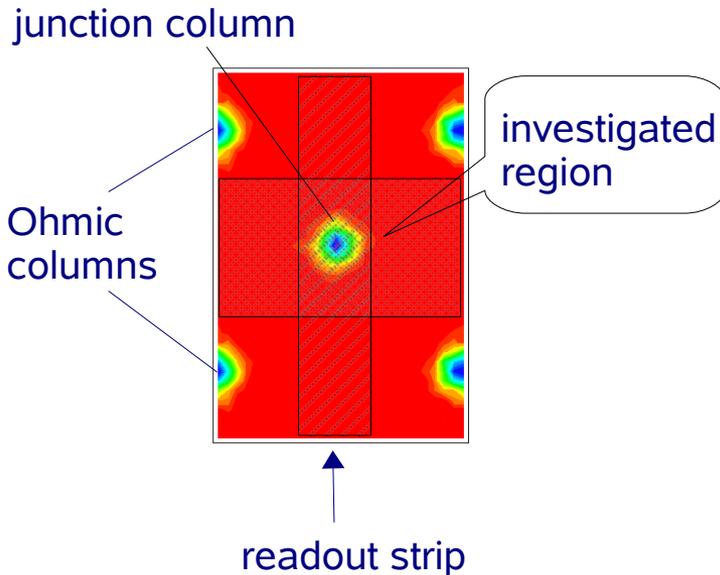
- From symmetry: **region with minimum electric field** is located in the middle of four columns



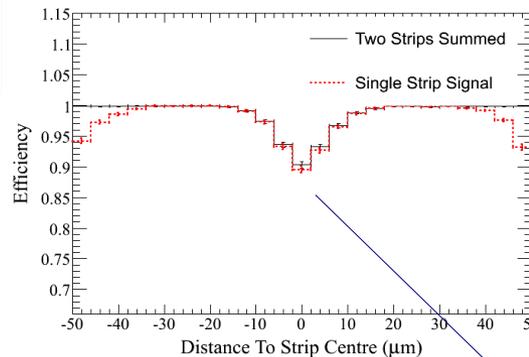
- Further investigation: uniformity of **efficiency in low field region**

Efficiency in Low Field Region

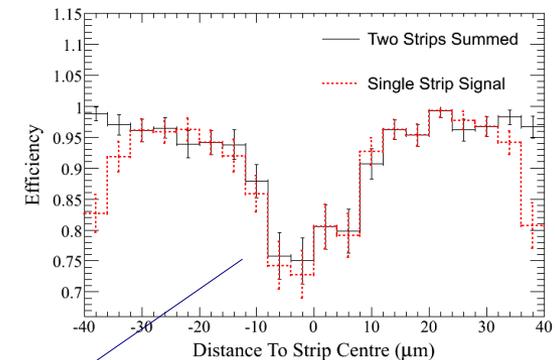
- To get a more quantitative view: consider **one-dimensional efficiency** in selected region
 - **Threshold: 2 fC**; exclude region around Ohmic column
 - Low field region located at left and right border of investigated region



FBK (40 V bias)



CNM (24 V bias)



junction column position

- In low field region: **no efficiency drop** observed when summing up signals of **two neighbouring strips**
 - Single strip signals: lower efficiency due to **charge sharing**

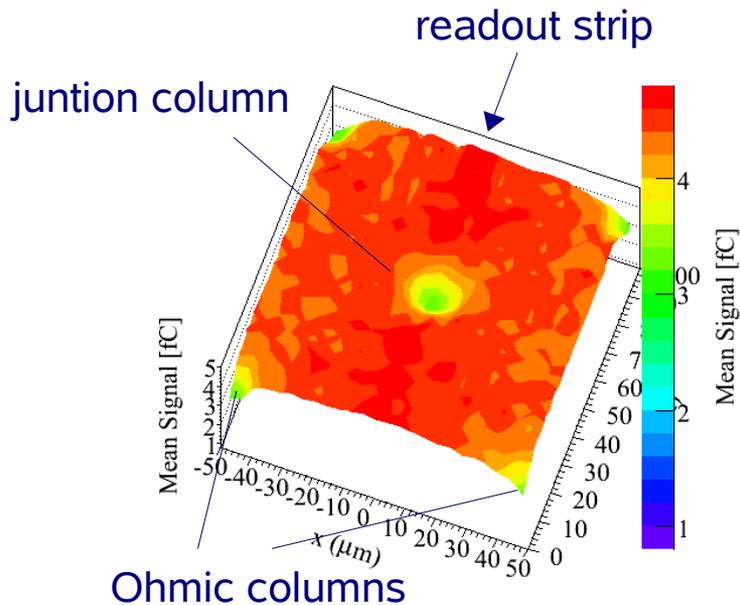
Conclusion / Outlook

- Measurements with first batch of 3D-DDTC (FBK and CNM) are promising:
 - **Full charge collected** in FBK sensor
 - Lower charge in CNM device (preliminary laboratory measurements with devices of second batch indicate full charge collection)
 - Apart from column positions: **efficiency uniform**
 - Improvement compared to 3D-STC (Single Type Column) detectors with columns of one doping type only
- Measurements performed with **50 ns shaping time** – lower signal expected for shorter shaping time (especially for the FBK sensor geometry due to small column overlap)
 - New batches of DDTC detectors (p-type, FBK: also deeper columns): full charge should be collected within 25 ns
- Outlook: **test beam with irradiated 3D and planar detectors** performed in summer 2009 – data to be analysed
 - Direct **comparison of radiation hardness** of 3D and planar sensors

Backup Slides

Charge Collection 2D (FBK)

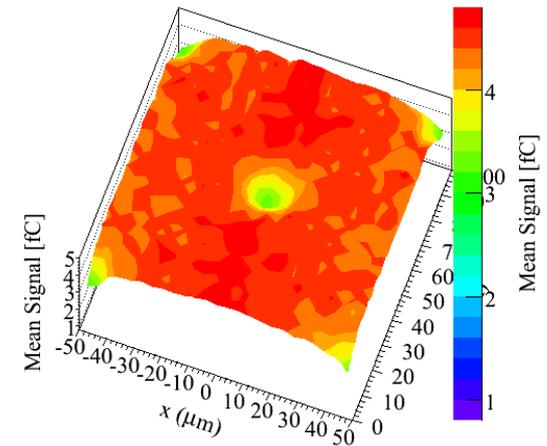
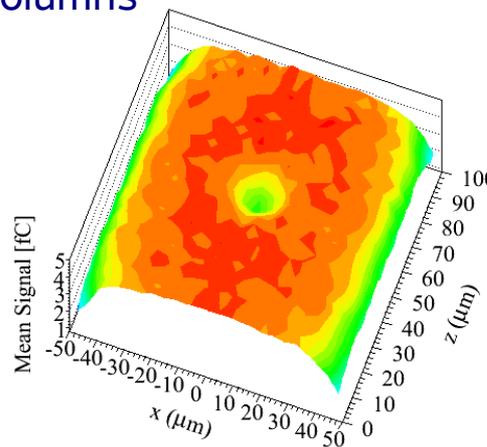
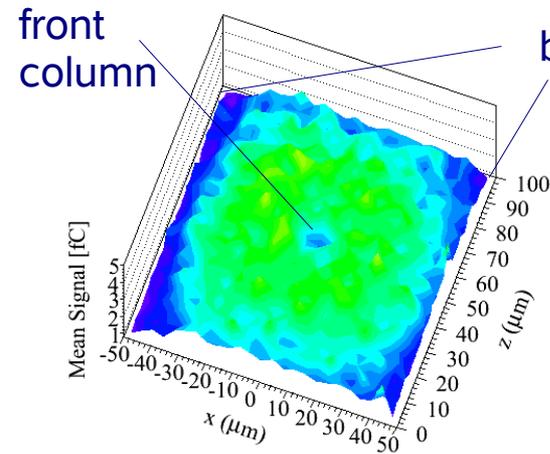
- Bias: 40 V
- Sensor divided into bins, **mean of measured signal** (not Landau MPV!) superimposed onto a unit cell
 - **Signal of two strips** closest to the track position summed up



- In column positions: lower signal

Charge Collection 2D

- Sensor divided into bins, **mean of measured signal** (not Landau MPV!) superimposed onto a unit cell
 - Growth of the depletion visible



- **5 V bias, signal of single strip**

Signal still low, confined to region around readout electrode (not yet fully depleted)

- **40 V bias, signal of single strip**

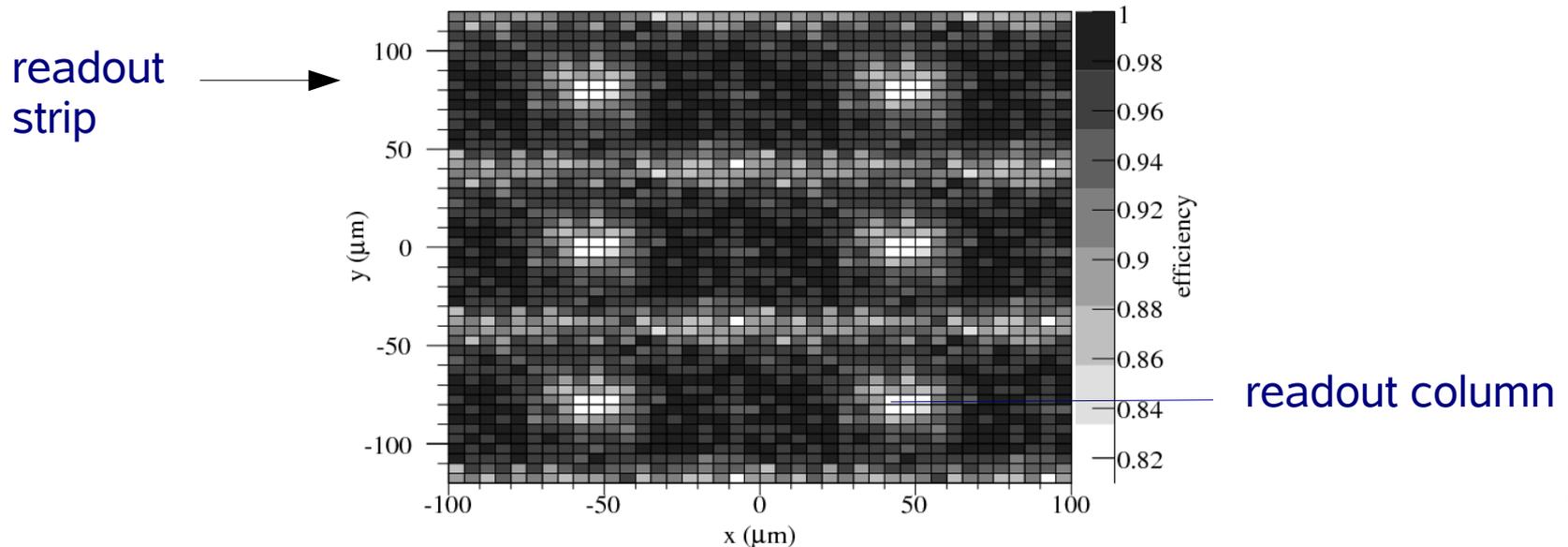
Charge sharing between readout strips

- **40 V bias, signal sum of two neighbouring strips**

Signal uniform (apart from the column positions)

2D Efficiency in 3D-STC

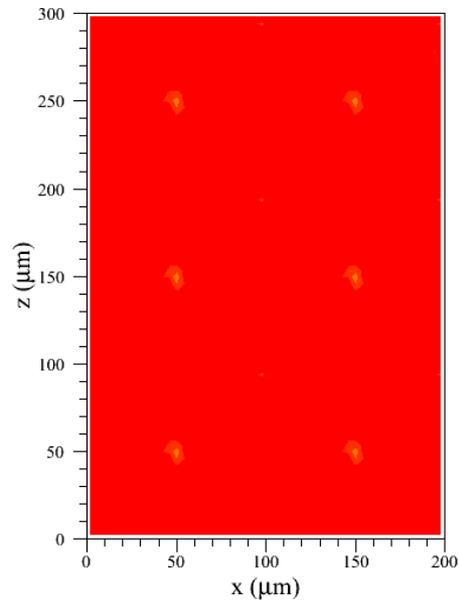
- Testbeam from 2007 with 3D-STC detectors [G. Pahn et al., IEEE TNS]
 - Efficiency: ratio of hits above threshold and total hits
 - **2D efficiency map** (40 V bias) with everything superimposed onto one unit cell and then plotted six times next to each other
 - Cut: deposited charge ≥ 1 fC
- Expressed **low field region** in the middle between strips visible



2D Efficiency, Different Thresholds

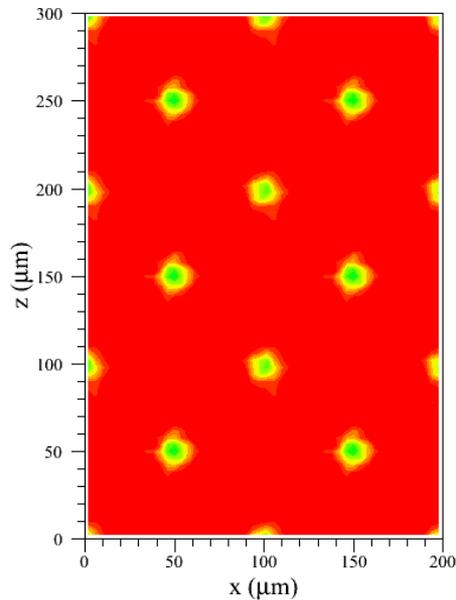
- Again: Signal of two strips summed, 40 V bias

1 fC



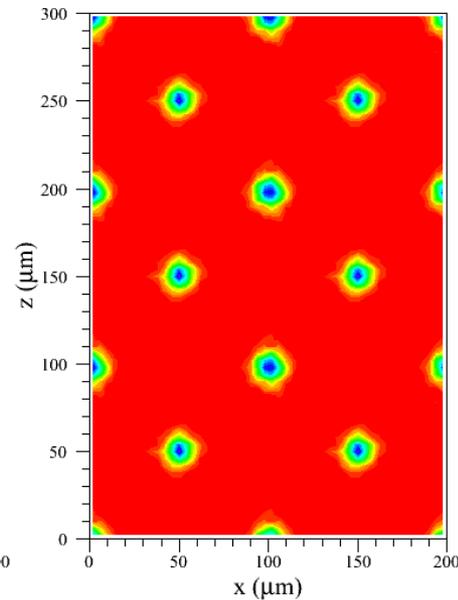
eff.: $(99.80 \pm 0.01)\%$

1.5 fC



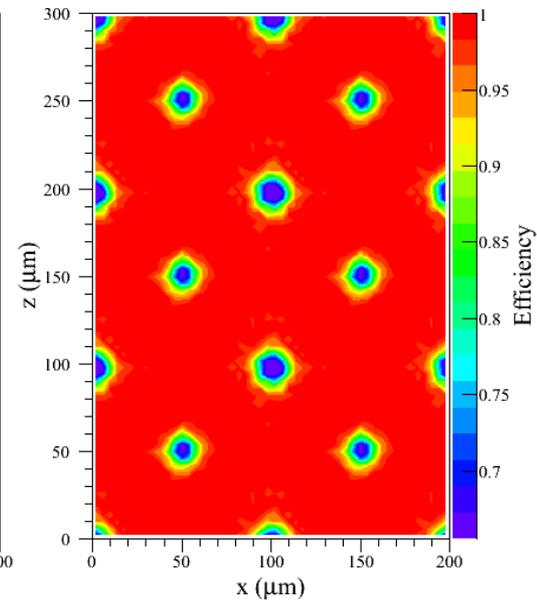
$(99.24 \pm 0.02)\%$

2 fC



$(98.53 \pm 0.03)\%$

2.5 fC



$(97.52 \pm 0.04)\%$